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APPLICATION NO.	FU	LING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/013,087	1	2/07/2001	Hideyuki Andoh	44471-267680 (13700) 1427	1427
23370	7590	03/07/2006		EXAM	INER
JOHN S. P.	•	•	SCHILLINGER, LAURA M		
	KILPATRICK STOCKTON, LLP 1100 PEACHTREE STREET				PAPER NUMBER
			ART UNIT	PAPER NUMBER	
ATLANTA,	GA 303	09	2813		

DATE MAILED: 03/07/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(a)			
	Application No.	Applicant(s)			
Office Action Summary	10/013,087	ANDOH, HIDEYUKI			
Office Action Summary	Examiner	Art Unit			
The MAN INC DATE of this communication	Laura M. Schillinger	2813			
The MAILING DATE of this communication Period for Reply A SHORTENED STATUTORY PERIOD FOR RE WHICHEVER IS LONGER, FROM THE MAILING - Extensions of time may be available under the provisions of 37 CFF after SIX (6) MONTHS from the mailing date of this communication - If NO period for reply is specified above, the maximum statutory per - Failure to reply within the set or extended period for reply will, by states that the mailing date of the maximum statutory per - Failure to reply within the set or extended period for reply will, by states and patent term adjustment. See 37 CFR 1.704(b). Status	PLY IS SET TO EXPIRE 3 MG B DATE OF THIS COMMUNIC R 1.136(a). In no event, however, may a retrict will apply and will expire SIX (6) MON atute, cause the application to become AB.	ONTH(S) OR THIRTY (30) DAYS, CATION. Poply be timely filed THS from the mailing date of this communication. ANDONED (35 U.S.C. § 133).			
	4 Danambar 2005				
1)⊠ Responsive to communication(s) filed on <u>1</u> . 2a)□ This action is FINAL . 2b)⊠ 1	<u>4 December 2005</u> . This action is non-final.				
<u> </u>	ince this application is in condition for allowance except for formal matters, prosecution as to the merits is				
closed in accordance with the practice und	•	• •			
·		·			
Disposition of Claims 4) Claim(s) 1-9 is/are pending in the application					
4a) Of the above claim(s) is/are without 5) ☐ Claim(s) is/are allowed. 6) ☑ Claim(s) <u>1-9</u> is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and					
Application Papers					
9) The specification is objected to by the Exam 10) The drawing(s) filed on is/are: a) Applicant may not request that any objection to Replacement drawing sheet(s) including the cor 11) The oath or declaration is objected to by the	accepted or b) objected to the drawing(s) be held in abeyand rection is required if the drawing(ce. See 37 CFR 1.85(a). s) is objected to. See 37 CFR 1.121(d).			
Priority under 35 U.S.C. § 119					
12) Acknowledgment is made of a claim for fore a) All b) Some * c) None of: 1. Certified copies of the priority docum 2. Certified copies of the priority docum 3. Copies of the certified copies of the papplication from the International But * See the attached detailed Office action for a	ents have been received. ents have been received in Appriority documents have been reau (PCT Rule 17.2(a)).	pplication No received in this National Stage			
Attachment(s)					
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) 	· —	ummary (PTO-413))/Mail Date			

U.S. Patent and Trademark Office PTOL-326 (Rev. 7-05)

3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)

Paper No(s)/Mail Date 12/24/05.

6) Other: _

5) Notice of Informal Patent Application (PTO-152)

DETAILED ACTION

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Allowability is hereby withdrawn, in view of newly discovered prior art.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-9 are rejected under 35 U.S.C. 102(b) as being anticipated by Yanagisawa (JP 58-085572).

In reference to claim 1, Yanagisawa teaches a device comprising:

A first semiconductor region of a first conductivity type, defined by an upper end surface and a side boundary surface connecting the upper and lower end surfaces when viewed in section (Fig.D (16));

A second semiconductor region of the first conductivity type disposed under the first semiconductor region and being in contact with the lower end surface of the first semiconductor region so as to share a common boundary surface by the first and second semiconductor regions (Fig.D (12));

A third semiconductor region of a second conductivity type disposed on the first semiconductor region and being in contact with the upper end surface of the first semiconductor region (Fig.D (18)); and

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A fourth semiconductor region having inner surface in contact with the first and second with the side boundary surface when viewed in section and an impurity concentration lower than the first semiconductor region, configured such that the fourth semiconductor region is disposed between the second and third semiconductor regions (Fig.D (13)) (see abstract).

In reference to claim 2, Yanagisawa teaches wherein the fourth semiconductor region has a first type conductivity (Fig.D (13)).

In reference to claim 3, Yanagisawa teaches wherein outer surface of the fourth semiconductor region serves as a chip outer surface of the semiconductor device and the chip outer surface is substantially orthogonal with the lower end surface of the first semiconductor region (Fig.D (13)).

In reference to claim 4, Yanagisawa teaches wherein the fourth semiconductor region is made of a wafer cut from bulk crystal (inherent- semiconductor substrates are made from wafers cut from bulk crystal).

In reference to claim 5, Yanagisawa teaches further comprising a first main electrode layer is formed on a bottom surface of the second semiconductor region (Fig.G (21)).

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In reference to claim 6, Yanagisawa teaches wherein the first main electrode layer is contacted with the second semiconductor region, through a first concavity formed at the bottom surface of the second semiconductor region (Fig.G (21)).

In reference to claim 7, Yanagisawa teaches further comprising a first main electrode layer, a part of the first main electrode layer is buried in a via hole penetrating through the second semiconductor region, configured such that the buried part of the first main electrode layer contacts with the first semiconductor region (Fig.G (21)).

In reference to claim 8, Yanagisawa teaches further comprising a second main electrode layer is formed on a top surface of the third semiconductor region (Fig.G (20)).

In reference to claim 9, Yanagisawa teaches wherein the second main electrode layer is contacted with the first semiconductor regions, through a second concavity formed at the top surface of the third semiconductor region (Fig.G (20)).

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Laura M. Schillinger whose telephone number is (571) 272-1697. The examiner can normally be reached on M-T, R-F 7:00-5:00.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl W. Whitehead, Jr. can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

02/27/06

Laura M Schillinger
Primary Examiner
Art Unit 2813